







SN54AC00-SP SCHS367C - OCTOBER 2008 - REVISED APRIL 2022

SN54AC00-SP Radiation Hardened Quad 2 Input NAND Gate

1 Features

- 5962R87549:
 - Radiation hardness assurance (RHA) up to TID 100 krad (Si)
 - SEL immune to 86 MeV×cm²/mg
- 5962-87549:
 - Total ionizing dose 50 krad (Si)
- 2 V to 6 V V_{CC} operation
- Inputs accept voltages to 6 V
- Maximum t_{pd} of 7 ns at 5 V

2 Applications

- Satellite payloads
- Satellite power on reset logic
- RHA known good Die (KGD) offering for space hybrids

Pin Functions (Each Gate)

INP	UTS	OUTPUT
Α	В	Y
Н	Н	L
L	X	н
X	L	н



Logic Diagram (Positive Logic)

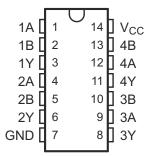
3 Description

The SN54AC00 device contains four independent 2input NAND gates. Each gate performs the Boolean function of $Y = \overline{A \cdot B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)		
	CDIP (14)	5.97 mm × 9.21 mm		
SN54AC00-SP	CFP (14)	6.67 mm × 19.56 mm		
	KGD (0)	Not applicable		

For all available packages, see the orderable addendum at the end of the data sheet.



J or W Package (Top View)



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	vision C (April 2022) Page s, and cross-references throughout the document1
 Removed SEU from the Features section 	1

Changes from Revision A (December 2013) to Revision B (February 2015)

	<u> </u>
•	Added KGD package information
•	Added Device and Documentation Support section and Mechanical, Packaging, and Orderable Information
	section1
•	Added Bare Die Information, image, and Bond Pad Coordinates in Microns
•	Added parameter information for KGD to Section 6.5 and Section 6.6

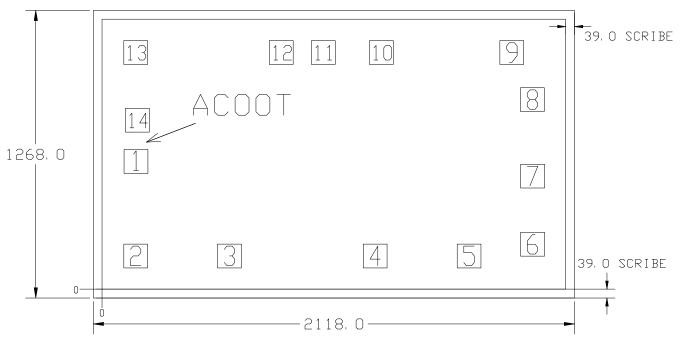
Changed SEL immune to 86 MeV×cm²/mg......1

Cł	hanges from Revision * (October 2008) to Revision A (December 2013)	Page
•	Changed Features bullets	1

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5 Bare Die Information

DIE THICKNESS	BACKSIDE FINISH	BACKSIDE POTENTIAL	BOND PAD METALLIZATION COMPOSITION	BOND PAD THICKNESS	
15 mils	Silicon with backgrind	Floating	TiW/AlCu2	15800 nm	



Bond Pad Coordinates in Microns

Bona i da Goordinates in Microns								
PAD NUMBER	X MIN	Y MIN	X MAX	Y MAX				
1	96.3	510.5	201.3	615.5				
2	95	94	200	199				
3	508	94	613	199				
4	1149	94	1254	199				
5	1562	94	1667	199				
6	1841.5	145.5	1946.5	250.5				
7	1841.5	445.5	1946.5	550.5				
8	1841	783	1946	888				
9	1750.5	991	1855.5	1096				
10	1176.5	991	1281.5	1096				
11	921	991	1026	1096				
12	736	991	841	1096				
13	95	991	200	1096				
14	102.5	692	207.5	797				
	1 2 3 4 5 6 7 8 9 10 11 12 13	1 96.3 2 95 3 508 4 1149 5 1562 6 1841.5 7 1841.5 8 1841 9 1750.5 10 1176.5 11 921 12 736 13 95	1 96.3 510.5 2 95 94 3 508 94 4 1149 94 5 1562 94 6 1841.5 145.5 7 1841.5 445.5 8 1841 783 9 1750.5 991 10 1176.5 991 11 921 991 12 736 991 13 95 991	1 96.3 510.5 201.3 2 95 94 200 3 508 94 613 4 1149 94 1254 5 1562 94 1667 6 1841.5 145.5 1946.5 7 1841.5 445.5 1946.5 8 1841 783 1946 9 1750.5 991 1855.5 10 1176.5 991 1281.5 11 921 991 1026 12 736 991 841 13 95 991 200				



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		,	MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	7	V
VI	Input voltage ⁽²⁾		-0.5	V _{CC} + 0.5	V
Vo	Output voltage ⁽²⁾		-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	$V_1 < 0$ or $V_1 > V_{CC}$		±20	mA
I _{OK}	Output clamp current	$V_O < 0$ or $V_O > V_{CC}$		±20	mA
I _O	Continuous output current	$V_O = 0$ to V_{CC}		±50	mA
	Continuous current through	CC or GND		±200	mA
TJ	Junction temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 Recommended Operating Conditions

			MIN	MAX	UNIT
V _{CC}	Supply voltage		2	6	V
		V _{CC} = 3 V	2.1		
V_{IH}	High-level input voltage	V _{CC} = 4.5 V	3.15		V
		V _{CC} = 5.5 V	3.85		
		V _{CC} = 3 V		0.9	
V_{IL}	Low-level input voltage	V _{CC} = 4.5 V		1.35	-
		V _{CC} = 5.5 V		1.65	
V _I	Input voltage	·	0	V _{CC}	V
Vo	Output voltage		0	V _{CC}	V
		V _{CC} = 3 V		12	
I _{OH}	High-level output current	V _{CC} = 4.5 V		24	mA
		V _{CC} = 5.5 V		24	
		V _{CC} = 3 V		12	
I _{OL}	Low-level output current	V _{CC} = 4.5 V		24	mA
		V _{CC} = 5.5 V		24	
Δt/Δν	Input transition rise or fall rate			8	ns/V
T _A	Operating free-air temperature		-55	125	°C

Product Folder Links: SN54AC00-SP

⁽²⁾ The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

6.3 Thermal Information

		SN54A	SN54AC00-SP		
	THERMAL METRIC ⁽¹⁾ (2)	J	W	UNIT	
		14 PINS	14 PINS		
R _{0JA}	Junction-to-ambient thermal resistance	83.1	125.4		
R _{0JC(top)}	Junction-to-case (top) thermal resistance	26.6	30.85		
R _{0JB}	Junction-to-board thermal resistance	47.9	43.4	°C/W	
ΨЈТ	Junction-to-top characterization parameter	N/A	N/A	_ C/VV	
ΨЈВ	Junction-to-board characterization parameter	N/A	N/A		
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A		

- (1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.
- (2) The package thermal impedance is calculated in accordance with JESD 51-7 and Mil Std 883 method 1012.1 (see www.JEDEC.org).

6.4 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

DADAMETED	TEST CONDITIONS	V	T _A = 25°C			MIN	MAX	UNIT
PARAMETER V _{OH}	TEST CONDITIONS	V _{CC}	MIN	TYP	MAX	IVIIIN	MAX	UNII
		3 V	2.9			2.9		
	I _{OH} = -50 μA	4.5 V	4.4			4.4		
		5.5 V	5.4			5.4		
V_{OH}	I _{OH} = -12 mA	3 V	2.56			2.4		V
	L = 24 mA	4.5 V	3.86			3.7		
	$I_{OH} = -24 \text{ mA}$	5.5 V	4.86			4.7		
	$I_{OH} = -50 \text{ mA}^{(1)}$	5.5 V				3.85		
		3 V			0.1		0.1	
	I _{OL} = 50 μA	4.5 V			0.1		0.1	
		5.5 V			0.1		0.1	
V_{OL}	I _{OL} = 12 mA	3 V			0.36		0.5	V
		4.5 V			0.36		0.5	
	I _{OL} = 24 mA	5.5 V	,		0.36		0.5	
	I _{OL} = 50 mA ⁽¹⁾	5.5 V					1.65	
l _l	V _I = V _{CC} or GND	5.5 V			±0.1		±1	μA
I _{CC}	V _I = V _{CC} or GND, I _O = 0	5.5 V			4		40	μA
Ci	V _I = V _{CC} or GND	5 V	,	2.6		,		pF

⁽¹⁾ Not more than one output should be tested at a time, and the duration of the test should not exceed 2 ms.

6.5 Switching Characteristics, $V_{CC} = 3.3 \text{ V}$

over recommended operating free-air temperature range, V_{CC} = 3.3 V ±0.3 V (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM	то	T,	_A = 25°C		MIN	MAX	UNIT
	(INPUT)	(OUTPUT)	MIN	TYP	MAX	IVIIIV IVIAA	IVIIN IVIAA	IN WAA
t _{PLH}	A or B	V	2	7	9.5	1	11	ns
t _{PHL}	AOID	, ,	1.5	5.5	8	1	9	115
t _{PLH} (KGD only) ⁽¹⁾	A or B	V	1	7	9.5	1	11	no
t _{PHL} (KGD only) ⁽¹⁾	AUID	Y	1	5.5	9.5	1	11	ns

⁽¹⁾ Specification limits for KGD are based on SMD 5962-8754903

6.6 Switching Characteristics, $V_{CC} = 5 V$

over recommended operating free-air temperature range, V_{CC} = 5 V ±0.5 V (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM	TO (OUTPUT)	Т	A = 25°C		MIN	MAX	UNIT
PARAIVIE I ER	(INPUT)		MIN	TYP	MAX		IVIAA	
t _{PLH}	A or B	Y	1.5	6	8	1	8.5	ns
t _{PHL}			1.5	4.5	6.5	1	7	
t _{PLH} (KGD only) ⁽¹⁾	A or B	Y	1.5	6	8	1	8.5	ns
t _{PHL} (KGD only) ⁽¹⁾			1.5	4.5	8	1	8.5	

⁽¹⁾ Specification limits for KGD are based on SMD 5962-8754903

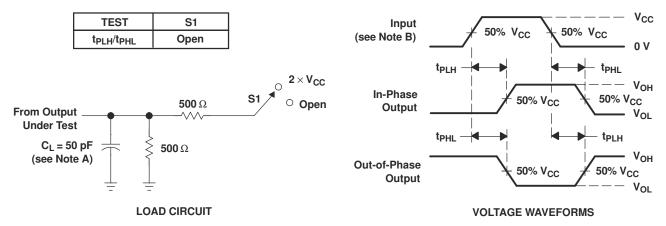
6.7 Operating Characteristics

 V_{CC} = 5 V, T_A = 25°C

PARAMETER	TEST CONDITIONS	TYP	UNIT	
C _{pd} Power dissipation capacitance	C _L = 50 pF, f = 1 MHz	40	pF	

Product Folder Links: SN54AC00-SP

7 Parameter Measurement Information



NOTES: A. C_L includes probe and jig capacitance.

- B. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, $Z_O = 50 \Omega$, $t_r \leq 2.5 \text{ ns}$, $t_f \leq 2.5 \text{ ns}$.
- C. The outputs are measured one at a time with one input transition per measurement.

Figure 7-1. Load Circuit and Voltage Waveforms



8 Device and Documentation Support

8.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

8.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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8.3 Trademarks

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8.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

9 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Product Folder Links: SN54AC00-SP

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing		Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
5962-8754903VCA	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8754903VC A SNV54AC00J	Samples
5962-8754903VDA	ACTIVE	CFP	W	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8754903VD A SNV54AC00W	Samples
5962R8754903V9A	ACTIVE	XCEPT	KGD	0	95	RoHS & Green	Call TI	N / A for Pkg Type	-55 to 125		Samples
5962R8754903VCA	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962R8754903VC A SNVR54AC00J	Samples
5962R8754903VDA	ACTIVE	CFP	W	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962R8754903VD A SNVR54AC00W	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

PACKAGE OPTION ADDENDUM

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(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN54AC00-SP:

Catalog: SN54AC00

NOTE: Qualified Version Definitions:

Catalog - TI's standard catalog product

PACKAGE MATERIALS INFORMATION

www.ti.com 10-Mar-2022

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
5962-8754903VDA	W	CFP	14	1	506.98	26.16	6220	NA
5962R8754903VCA	J	CDIP	14	25	506.98	15.24	13440	NA
5962R8754903VDA	W	CFP	14	1	506.98	26.16	6220	NA

W (R-GDFP-F14)

CERAMIC DUAL FLATPACK



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only.
- E. Falls within MIL STD 1835 GDFP1-F14



CERAMIC DUAL IN LINE PACKAGE



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4040083-5/G





CERAMIC DUAL IN LINE PACKAGE



NOTES:

- 1. All controlling linear dimensions are in inches. Dimensions in brackets are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This package is hermitically sealed with a ceramic lid using glass frit.
- His package is remitted by sealed with a ceramic its using glass mit.
 Index point is provided on cap for terminal identification only and on press ceramic glass frit seal only.
 Falls within MIL-STD-1835 and GDIP1-T14.



CERAMIC DUAL IN LINE PACKAGE



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